

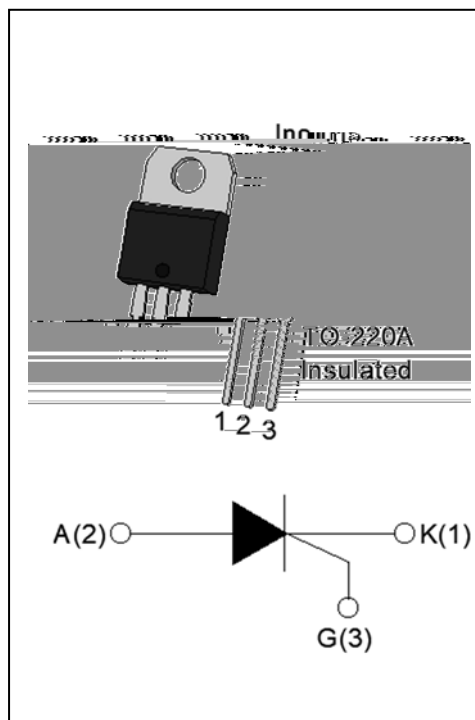


## JX080A 8A Sensitive SCR

Rev.A.1.0

### DESCRIPTION:

The JX080A SCR provides high  $dV/dt$  rate with strong resistance to electromagnetic interference. It is especially recommended for use on residual current circuit breaker, straight hair, igniter etc. By using an internal ceramic pad, JX080A provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.



### MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
$V_{DRM} / V_{RRM}$	800	V
$I_{GT}$	200	$\mu A$

### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	
Operating junction temperature range	$T_j$	-40-110	
Repetitive peak off-state voltage ( $T_j=25^\circ C$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ C$ )	$V_{RRM}$	800	V
Average on-state current ( $T_c = 82^\circ C$ )	$I_{T(AV)}$	5	A
RMS on-state current ( $T_c = 82^\circ C$ )	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current ( $t_p=10ms, T_j=25^\circ C$ )	$I_{TSM}$	80	A
Non repetitive surge peak on-state current ( $t_p=8.3ms, T_j=25^\circ C$ )		88	
$I^2t$ value for fusing ( $t_p=10ms, T_j=25^\circ C$ )	$I^2t$	32	$A^2s$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}, f=100Hz, T_j=110^\circ C$ )	$di/dt$	100	$A/\mu s$
Peak gate current ( $t_p=20\mu s, T_j=110^\circ C$ )	$I_{GM}$	4	A

Average gate power dissipation ( $T_j=110$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive,off-state;FIG.7)	$V_{pp}$	0.5	kV

**ELECTRICAL CHARACTERISTICS**

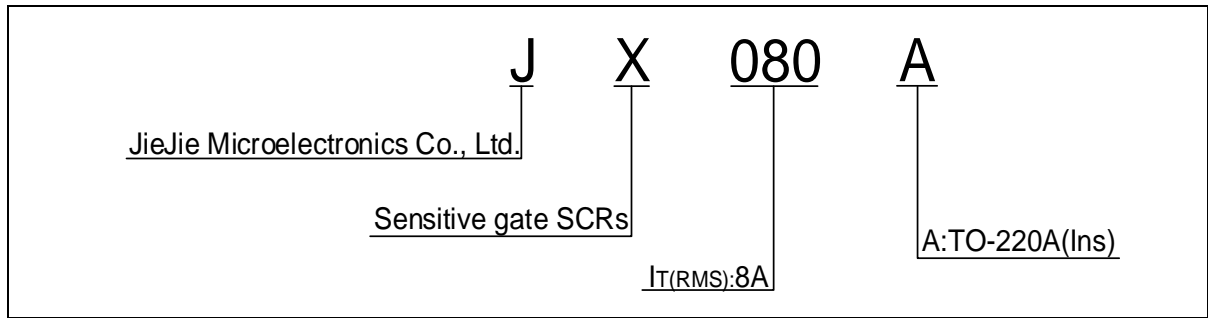
unless otherwise specified

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12V R_L=33$	-	60	200	$\mu A$
$V_{GT}$		-	-	0.8	V
$V_{GD}$	$V_D=V_{DRM} T_j=110$	0.2	-	-	V
$I_L$	$I_G=1.2 I_{GT}$	-	-	6	mA
$I_H$	$I_T=0.05A$	-	-	5	mA
dV/dt	$V_D=540V T_j=110 R_{GK}=1K$	50	-	-	V/ $\mu s$
	$V_D=540V T_j=110 R_{GK}=220$	200	-	-	
$t_{on}$	$I_G=10mA I_A=20mA I_R=2mA$	-	2	-	$\mu s$
$t_{off}$	$T_j=25$	-	70	-	$\mu s$

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_T=16A t_p=380\mu s$	$T_j=25$	1.6	V
$V_{TO}$	Threshold voltage	$T_j=110$	0.79	V
$R_D$	Dynamic Resistance	$T_j=110$	0.04	
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	$\mu$

ORDERING INFORMATION



MARKING

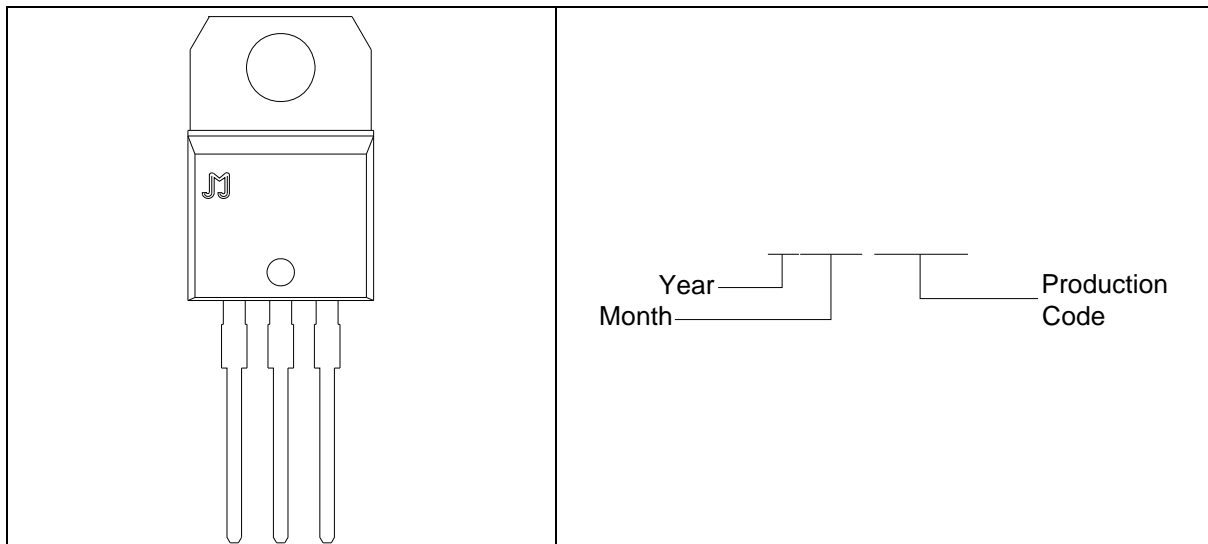
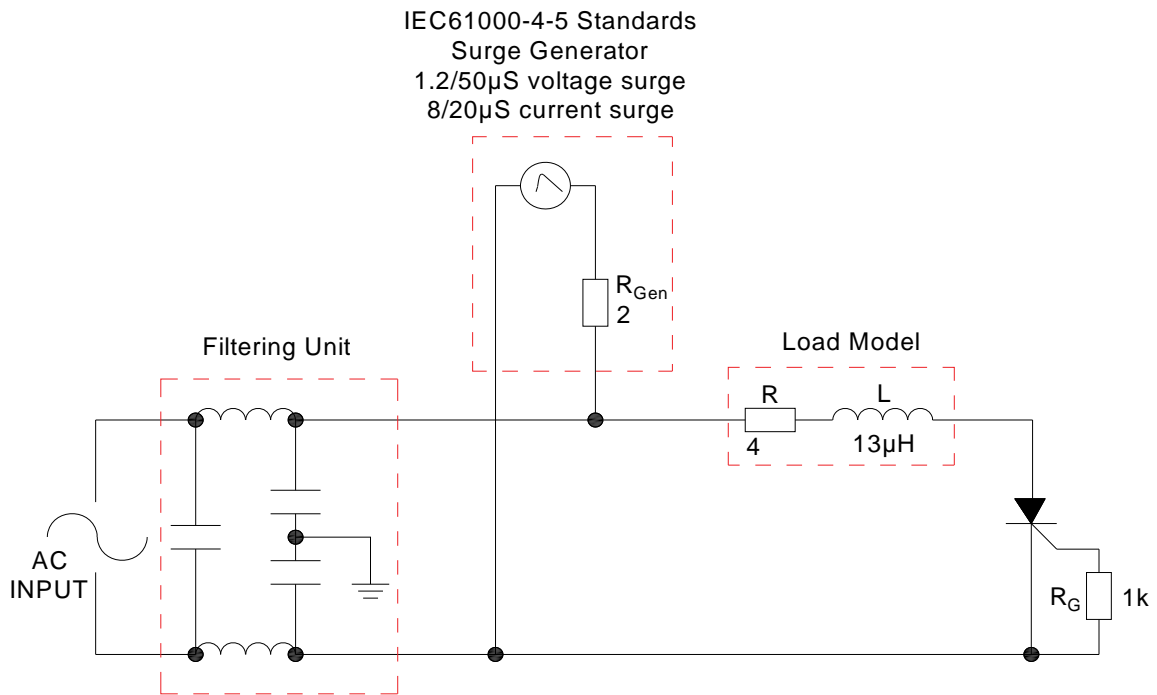




FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



## SHAPING AND SOLDERING PARAMETERS

Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie

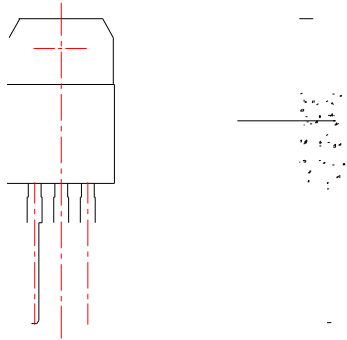
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT( $\mu$ A)	Package	Base qty. (pcs)	Delivery mode
JX080A	800	200	TO-220A(Ins)	50	Tube


**Document Revision History**

Date	Revision	Changes
May.18, 2023	A.1.0	Last update

PACKAGE MECHANICAL DATA 



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